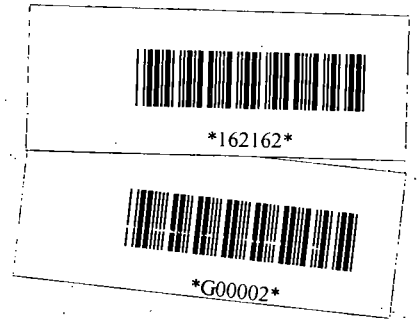


**ABSTRACT**

The invention relates to an RF impedance transformer (128) having a parallel low-impedance access Eb and serial high-impedance access Eh and intended for connection onto a printed circuit (130). The transformer comprises a multilayer circuit (60) that comprises a long side (64) and at least three layers. A first outer layer is separated from a second outer layer of the same thickness by at least one inner layer having a thickness at least four times greater than the thickness of the outer layers; each outer layer comprising an electrical conductor on each surface for forming a microstrip line (L1, L2), the serial high-impedance access Eh and the parallel low-impedance access Eb being on the long side (64) of the multilayer circuit (60) and near to each other so as to limit the area for connection with the printed circuit (130). The invention is for use for impedance transformers for HF amplifiers and circuits.

Figure 6